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# INTEGRATED CIRCUITS, SILICON MONOLITHIC, HCMOS DECADE COUNTER/DIVIDER WITH FULLY BUFFERED OUTPUTS

# **BASED ON TYPE 54HC4017**

ESCC Detail Specification No. 9204/072

Issue 4	October 2015
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# **DOCUMENTATION CHANGE NOTICE**

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DCR No.	CHANGE DESCRIPTION
946	Specification upissued to incorporate editorial changes per DCR.



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#### 1 <u>GENERAL</u>

#### 1.1 <u>SCOPE</u>

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

#### 1.2 <u>APPLICABLE DOCUMENTS</u>

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 9000.
- (b) MIL-STD-883, Test Methods and Procedures for Microelectronics.

#### 1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

#### 1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 <u>The ESCC Component Number</u> The ESCC Component Number shall be constituted as follows:

Example: 920407201F

- Detail Specification Reference: 9204072
- Component Type Variant Number: 01 (as required)
- Total Dose Radiation Level Letter: F (as required)

#### 1.4.2 <u>Component Type Variants</u>

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Terminal Material and/or Finish	Weight max g	Total Dose Radiation Level Letter
01	54HC4017	FP	G2	0.7	F [50kRAD(Si)]
02	54HC4017	FP	G4	0.7	F [50kRAD(Si)]
05	54HC4017	CCP	2	0.6	F [50kRAD(Si)]
10	54HC4017	DIP	G2	2.2	F [50kRAD(Si)]
11	54HC4017	DIP	G4	2.2	F [50kRAD(Si)]
12	54HC4017	SO	G2	0.7	F [50kRAD(Si)]
13	54HC4017	SO	G4	0.7	F [50kRAD(Si)]

The terminal material and/or finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.



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The total dose radiation level letter shall be as defined in ESCC Basic Specification No. 22900. If an alternative radiation test level is specified in the Purchase Order the letter shall be changed accordingly.

#### 1.5 <u>MAXIMUM RATINGS</u>

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Units	Remarks
Supply Voltage	$V_{DD}$	-0.5 to 7	V	Note 1
Input Voltage	V <sub>IN</sub>	-0.5 to V <sub>DD</sub> +0.5	V	Notes 1, 2
Output Voltage	V <sub>OUT</sub>	-0.5 to V <sub>DD</sub> +0.5	V	Notes 1, 3
Device Power Dissipation (Continuous)	P <sub>D</sub>	300	mW	Note 4
Supply Current	I <sub>DDop</sub>	50	mA	
Operating Temperature Range	T <sub>op</sub>	-55 to +125	°C	$T_{amb}$
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C	
Soldering Temperature For FP, DIP and SO For CCP	T <sub>sol</sub>	+265 +245	°C	Note 5 Note 6

#### NOTES:

- 1. Device is functional for  $2V \le V_{DD} \le 6V$ .
- 2. Input current limited to  $I_{IC} = \pm 20$ mA.
- 3. Output current limited to  $I_{OUT} = \pm 25$ mA.
- 4. The maximum device dissipation is determined by  $I_{DDop}$  max (50mA) × 6V.
- 5. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same terminal shall not be resoldered until 3 minutes have elapsed.
- 6. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

#### 1.6 HANDLING PRECAUTIONS

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are categorised as Class 2 per ESCC Basic Specification No. 23800 with a Minimum Critical Path Failure Voltage of 2500 Volts.

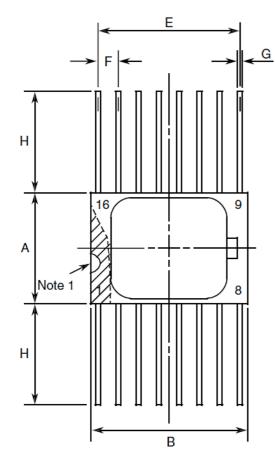


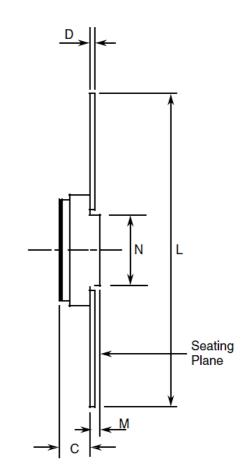
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1.7 <u>PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION</u> Consolidated Notes are given following the case drawings and dimensions.

## 1.7.1 Flat Package (FP) - 16 Pin



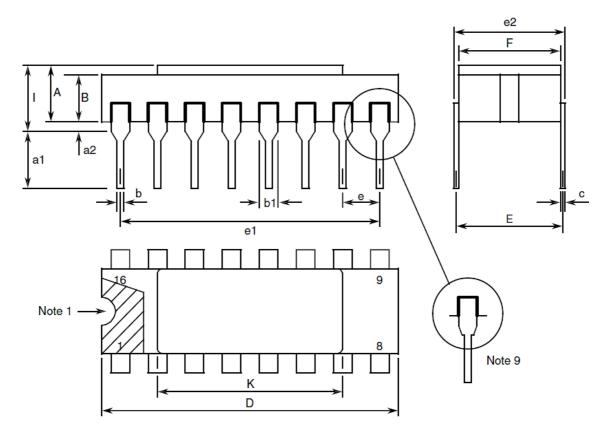


Cumhala	Dimensions mm		Natao
Symbols	Min	Max	Notes
A	6.75	7.06	
В	9.76	10.14	
С	1.49	1.95	
D	0.1	0.15	5
E	8.76	9.01	
F	1.27 BSC		3, 6
G	0.38	0.48	5
Н	6	-	5
L	18.75	22	
М	0.33	0.43	
Ν	4.32 TYPICAL		



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# 1.7.2 <u>Dual-in-line Package (DIP) - 16 Pin</u>



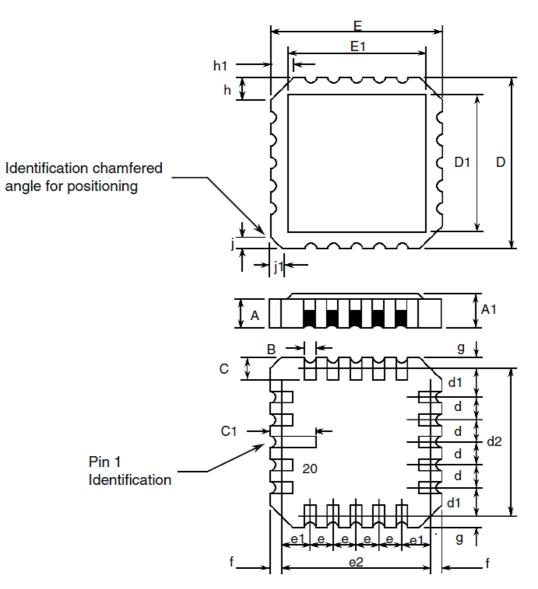
Symbolo	Dimensions mm		Nataa
Symbols	Min	Max	- Notes
A	2.1	2.71	
a1	3	3.7	
a2	0.63	1.14	2
В	1.82	2.39	
b	0.4	0.5	5
b1	1.14	1.5	5
с	0.2	0.3	5
D	20.06	20.58	
E	7.36	7.87	
е	2.54	BSC	4, 6
e1	17.65	17.9	
e2	7.62	8.12	
F	7.29	7.7	
I	-	3.83	



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Symbolo	Dimensi	ons mm	Notos
Symbols	Min	Max	Notes
К	10.9	12.1	

# 1.7.3 Chip Carrier Package (CCP) - 20 Terminal



Symbols	Dimensi	Natao	
	Min	Max	Notes
A	1.14	1.95	
A1	1.63	2.36	
В	0.55	0.72	5
С	1.06	1.47	5

ESCC Detail Specification



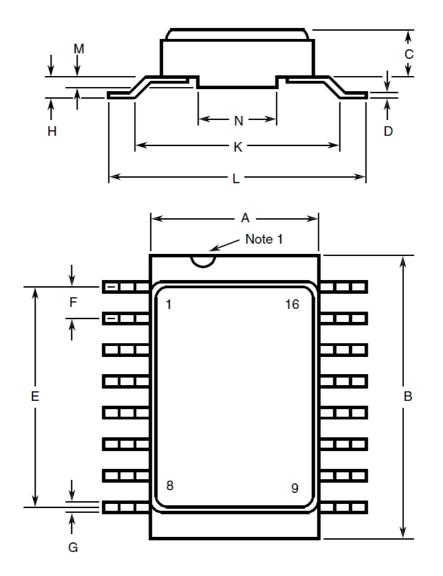
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C: mah ala	Dimensions mm		Natas
Symbols	Min	Max	
C1	1.91	2.41	
D	8.67	9.09	
D1	7.21	7.52	
d, d1	1.27 BSC		3
d2	7.62 BSC		
E	8.67	9.09	
E1	7.21	7.52	
e, e1	1.27 BSC		3
e2	7.62 BSC		
f, g	- 0.76		
h, h1	1.01 TYPICAL		8
j, j1	0.51 TYPICAL		7

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# 1.7.4 <u>Small Outline Ceramic Package (SO) - 16 Pin</u>



Symbolo	Dimensions mm		Notoo
Symbols	Min	Max	Notes
A	6.75	7.06	
В	9.76	10.14	
С	1.49	1.95	
D	0.1	0.15	5
E	8.76	9.01	
F	1.27 BSC		3, 6
G	0.38	0.48	5
Н	0.6	0.9	5
к	9 TYPICAL		





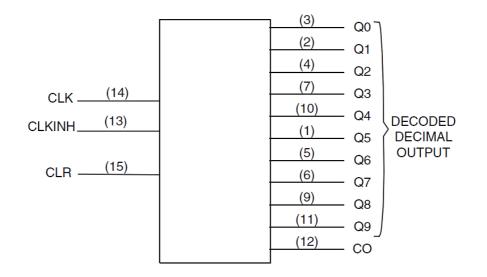
Symbols	Dimensi	ons mm	Notoo		
Symbols	Min	Max	Notes		
L	10	10.65			
М	0.33	0.43			
N	4.31 TY	4.31 TYPICAL			

#### 1.7.5 <u>Notes to Physical Dimensions and Terminal Identification</u>

- 1. Index area; a notch or a dot shall be located adjacent to Pin 1 and shall be within the shaded area shown. For chip carrier packages, the index shall be as shown.
- 2. The dimension shall be measured from the seating plane to the base plane.
- 3. The true position pin spacing is 1.27mm between centrelines. Each pin centreline shall be located within ±0.13mm of its true longitudinal position relative to Pin 1 and the highest pin number.
- 4. The true position pin spacing is 2.54mm between centrelines. Each pin centreline shall be located within ±0.25mm of its true longitudinal position relative to Pin 1 and the highest pin number.
- 5. All terminals.
- 6. 14 spaces.
- 7. Index corner only 2 dimensions.
- 8. 3 non-index corners 6 dimensions.
- 9. For all pins, either pin shape may be supplied.

#### 1.8 FUNCTIONAL DIAGRAM

Pin numbers relate to FP, DIP and SO packages only.





#### 1.9 PIN ASSIGNMENT

Dia	Func	tion	Dim	Fund	tion
Pin	FP, DIP and SO	CCP	Pin	FP, DIP and SO	CCP
1	Q5 Output	-	11	Q9 Output	-
2	Q1 Output	Q5 Output	12	CO Output (Carry Out)	Q8 Output
3	Q0 Output	Q1 Output	13	CLKINH Input (Clock Inhibit)	Q4 Output
4	Q2 Output	Q0 Output	14	CLK Input (Clock)	Q9 Output
5	Q6 Output	Q2 Output	15	CLR Input (Clear)	CO Output (Carry Out)
6	Q7 Output	-	16	V <sub>DD</sub>	-
7	Q3 Output	Q6 Output	17	-	CLKINH Input (Clock Inhibit)
8	V <sub>SS</sub>	Q7 Output	18	-	CLK Input (Clock)
9	Q8 Output	Q3 Output	19	-	CLR Input (Clear)
10	Q4 Output	$V_{SS}$	20	-	V <sub>DD</sub>

#### 1.10 TRUTH TABLE AND TIMING CHART

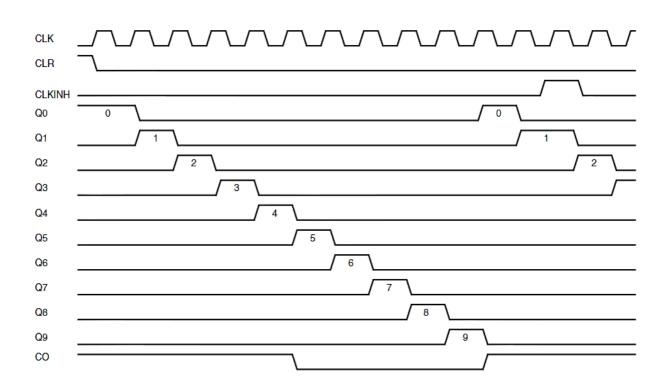
Logic Level Definitions: L = Low Level, H = High Level, X = Irrelevant.
 ↑ = Transition, Low to High; ↓ = Transition, High to Low.

	INPUTS		OUTPUTS
CLR	CLK	CLKINH	
Н	Х	Х	CLEAR (Q0 = H ; Q1 to Q9 = L)
L	↑	L	COUNTER ADVANCES
L	Н	$\downarrow$	COUNTER ADVANCES
L	L	Х	NO CHANGE
L	Х	Н	NO CHANGE
L	Н	↑	NO CHANGE
L	$\downarrow$	L	NO CHANGE



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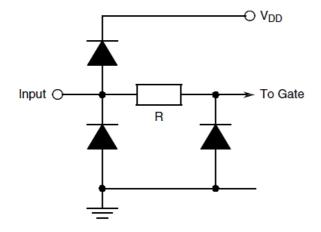
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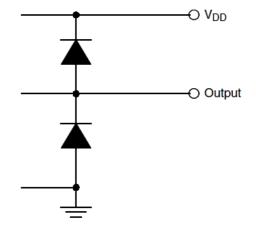


# 1.11 PROTECTION NETWORKS

INPUT PROTECTION

OUTPUT PROTECTION







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#### 2 <u>REQUIREMENTS</u>

#### 2.1 <u>GENERAL</u>

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

#### 2.1.1 <u>Deviations from the Generic Specification</u> None.

#### 2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) Terminal identification.
- (b) The ESCC qualified components symbol (for ESCC qualified components only).
- (c) The ESCC Component Number.
- (d) Traceability information.

#### 2.3 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures. Consolidated Notes are given after the tables.

#### 2.3.1 <u>Room Temperature Electrical Measurements</u>

The measurements shall be performed at  $T_{amb}$  = +22 ±3°C.

Characteristics			Lin	nits	Units	
		Test Method	Note 1	Min	Max	
Functional Test 1	-	3014	Verify Truth Table without Load $V_{IL} = 0.3V, V_{IH} = 1.5V$ $V_{DD} = 2V, V_{SS} = 0V$ $t_r < 1\mu s$ Note 2	-	-	-
Functional Test 2	-	3014	Verify Truth Table without Load $V_{IL} = 0.9V, V_{IH} = 3.15V$ $V_{DD} = 4.5V, V_{SS} = 0V$ $t_r = t_f < 500ns$ Note 2	-	-	-



Characteristics	Symbols	MIL-STD-883	Test Conditions	Lin	nits	Units
		Test Method	Note 1	Min	Max	
Functional Test 3	-	3014	Verify Truth Table without Load $V_{IL} = 1.2V, V_{IH} = 4.2V$ $V_{DD} = 6V, V_{SS} = 0V$ $t_r = t_f < 400ns$ Note 2	-	-	-
Quiescent Current	I <sub>DD</sub>	3005	$V_{IL} = 0V, V_{IH} = 6V$ $V_{DD} = 6V, V_{SS} = 0V$ All Outputs Open Note 3	-	400	nA
Low Level Input Current	IIL	3009	$V_{IN}$ (Under Test) = 0V $V_{IN}$ (Remaining Inputs) = 6V $V_{DD}$ = 6V, $V_{SS}$ = 0V	-	-50	nA
High Level Input Current	I <sub>IH</sub>	3010	$V_{IN}$ (Under Test) = 6V $V_{IN}$ (Remaining Inputs) = 0V $V_{DD}$ = 6V, $V_{SS}$ = 0V	-	50	nA
Low Level Output Voltage 1	V <sub>OL1</sub>	3007	$V_{IL} = 0.3V, V_{IH} = 1.5V$ $I_{OL} = 20\mu A$ $V_{DD} = 2V, V_{SS} = 0V$	-	100	mV
Low Level Output Voltage 2	V <sub>OL2</sub>	3007		-	100	mV
Low Level Output Voltage 3	V <sub>OL3</sub>	3007	$V_{IL} = 1.2V, V_{IH} = 4.2V$ $I_{OL} = 20\mu A$ $V_{DD} = 6V, V_{SS} = 0V$	-	100	mV
Low Level Output Voltage 4	V <sub>OL4</sub>	3007	$V_{IL} = 0.9V, V_{IH} = 3.15V$ $I_{OL} = 4mA$ $V_{DD} = 4.5V, V_{SS} = 0V$	-	260	mV
Low Level Output Voltage 5	V <sub>OL5</sub>	3007	$V_{IL} = 1.2V, I_{IH} = 4.2V$ $I_{OL} = 5.2mA$ $V_{DD} = 6V, V_{SS} = 0V$	-	260	mV
High Level Output Voltage 1	V <sub>OH1</sub>	3006	$V_{IL} = 0.3V, V_{IH} = 1.5V$ $I_{OH} = -20\mu A$ $V_{DD} = 2V, V_{SS} = 0V$	1.9	-	V
High Level Output Voltage 2	V <sub>OH2</sub>	3006	$V_{IL} = 0.9V, V_{IH} = 3.15V$ $I_{OH} = -20\mu A$ $V_{DD} = 4.5V, V_{SS} = 0V$	4.4	-	V
High Level Output Voltage 3	V <sub>OH3</sub>	3006	$V_{IL} = 1.2V, V_{IH} = 4.2V$ $I_{OH} = -20\mu A$ $V_{DD} = 6V, V_{SS} = 0V$	5.9	-	V
High Level Output Voltage 4	V <sub>OH4</sub>	3006	$V_{IL} = 0.9V, V_{IH} = 3.15V$ $I_{OH} = -4mA$ $V_{DD} = 4.5V, V_{SS} = 0V$	3.98	-	V
High Level Output Voltage 5	V <sub>OH5</sub>	3006	$V_{IL} = 1.2V, V_{IH} = 4.2V$ $I_{OH} = -5.2mA$ $V_{DD} = 6V, V_{SS} = 0V$	5.48	-	V



Characteristics	Symbols	MIL-STD-883	Test Conditions	Lin	nits	Units
		Test Method	Note 1	Min	Max	
Threshold Voltage N-Channel	V <sub>THN</sub>	-	CLKINH Input at Ground All Other Inputs: $V_{IN} = 5V$ $V_{DD} = 5V$ , $I_{SS} = -10\mu A$	-0.45	-1.45	V
Threshold Voltage P-Channel	V <sub>THP</sub>	-	CLKINH Input at Ground All Other Inputs: $V_{IN} = -5V$ $V_{SS} = -5V$ , $I_{DD} = 10\mu A$	0.45	1.35	V
Input Clamp Voltage 1, to V <sub>SS</sub>	V <sub>IC1</sub>	-	I <sub>IN</sub> (Under Test) = -100µA V <sub>DD</sub> = Open, V <sub>SS</sub> = 0V All Other Pins Open	-400	-900	mV
Input Clamp Voltage 2, to V <sub>DD</sub>	V <sub>IC2</sub>	-	I <sub>IN</sub> (Under Test) = 100µA V <sub>DD</sub> = 0V, V <sub>SS</sub> = Open All Other Pins Open	400	900	mV
Input Capacitance	C <sub>IN</sub>	3012	$V_{IN}$ (Not Under Test) = 0V $V_{DD} = V_{SS} = 0V$ f = 100kHz to 1MHz Note 4	-	10	pF
Propagation Delay Low to High, CLK to Q0	t <sub>PLH1</sub>	3003	$V_{IN} \text{ (Under Test)} = \text{Pulse}$ Generator $V_{IN} \text{ (Remaining Inputs)}$ = Truth Table $V_{IL} = 0V, V_{IH} = 4.5V$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 5	-	46	ns
Propagation Delay High to Low, CLK to Q0	t <sub>PHL1</sub>	3003		-	46	ns
Propagation Delay Low to High, CLKINH to Q0	t <sub>PLH2</sub>	3003		-	50	ns



Characteristics	Symbols	MIL-STD-883	Test Conditions	Lin	nits	Units
		Test Method	Note 1	Min	Max	
Propagation Delay High to Low, CLKINH to Q0	t <sub>PHL2</sub>	3003	$V_{IN} (Under Test) = Pulse$ Generator $V_{IN} (Remaining Inputs)$ = Truth Table $V_{IL} = 0V, V_{IH} = 4.5V$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 5	-	50	ns
Propagation Delay Low to High, CLK to CO	t <sub>PLH3</sub>	3003	$V_{IN} (Under Test) = Pulse$ Generator $V_{IN} (Remaining Inputs)$ = Truth Table $V_{IL} = 0V, V_{IH} = 4.5V$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 5	-	46	ns
Propagation Delay High to Low, CLK to CO	t <sub>PHL3</sub>	3003		-	46	ns
Propagation Delay Low to High, CLKINH to CO	t <sub>PLH4</sub>	3003	$V_{IN} (Under Test) = Pulse$ Generator $V_{IN} (Remaining Inputs)$ = Truth Table $V_{IL} = 0V, V_{IH} = 4.5V$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 5	-	50	ns
Propagation Delay High to Low, CLKINH to CO	t <sub>PHL4</sub>	3003	$V_{IN} (Under Test) = Pulse$ Generator $V_{IN} (Remaining Inputs)$ = Truth Table $V_{IL} = 0V, V_{IH} = 4.5V$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 5	-	50	ns
Propagation Delay Low to High, CLR to Q0	t <sub>PLH5</sub>	3003	$V_{IN} (Under Test) = Pulse$ Generator $V_{IN} (Remaining Inputs)$ = Truth Table $V_{IL} = 0V, V_{IH} = 4.5V$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 5	-	46	ns
Propagation Delay High to Low, CLR to CO	t <sub>PHL6</sub>	3003	$V_{IN} (Under Test) = Pulse$ Generator $V_{IN} (Remaining Inputs)$ = Truth Table $V_{IL} = 0V, V_{IH} = 4.5V$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 5	-	46	ns



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Characteristics	Symbols	MIL-STD-883	Test Conditions	Limits		Units
		Test Method	Note 1	Min	Max	
Transition Time Low to High, Q0	t <sub>TLH</sub>	3004		-	15	ns
Transition Time High to Low, Q0	t <sub>THL</sub>	3004	$V_{IN} \text{ (Under Test)} = \text{Pulse}$ Generator $V_{IN} \text{ (Remaining Inputs)}$ = Truth Table $V_{IL} = 0V, V_{IH} = 4.5V$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 5	-	15	ns
Maximum Clock Frequency	f <sub>CLK</sub>	-	$V_{IN} (CLK) = Pulse$ Generator $V_{IL} = 0V, V_{IH} = 4.5V$ $V_{DD} = 4.5V, V_{SS} = 0V$ Notes 6, 7	25	-	MHz

# 2.3.2 <u>High and Low Temperatures Electrical Measurements</u>

The measurements shall be performed at  $T_{amb}$ =+125 (+0 -5)°C and  $T_{amb}$ =- 55(+5-0)°C.

Characteristics	Symbols	MIL-STD-883	Test Conditions	Lin	nits	Units
		Test Method	Note 1	Min	Max	
Functional Test 1	-	3014	Verify Truth Table without Load $V_{IL} = 0.3V, V_{IH} = 1.5V$ $V_{DD} = 2V, V_{SS} = 0V$ $t_r < 1\mu s$ Note 2	-	-	-
Functional Test 2	-	3014	Verify Truth Table without Load $V_{IL} = 0.9V, V_{IH} = 3.15V$ $V_{DD} = 4.5V, V_{SS} = 0V$ $t_r = t_f < 500ns$ Note 2	-	-	-
Functional Test 3	-	3014	Verify Truth Table without Load $V_{IL} = 1.2V, V_{IH} = 4.2V$ $V_{DD} = 6V, V_{SS} = 0V$ $t_r = t_f < 400ns$ Note 2	-	-	-
Quiescent Current	I <sub>DD</sub>	3005	$V_{IL} = 0V, V_{IH} = 6V$ $V_{DD} = 6V, V_{SS} = 0V$ All Outputs Open Note 3	-	8	μA



Characteristics	Symbols	MIL-STD-883	Test Conditions	Lin	nits	Units
		Test Method	Note 1	Min	Max	
Low Level Input Current	IIL	3009	$V_{IN}$ (Under Test) = 0V $V_{IN}$ (Remaining Inputs) = 6V $V_{DD}$ = 6V, $V_{SS}$ = 0V	-	-1	μA
High Level Input Current	I <sub>IH</sub>	3010	$V_{IN}$ (Under Test) = 6V $V_{IN}$ (Remaining Inputs) = 0V $V_{DD}$ = 6V, $V_{SS}$ = 0V	-	1	μA
Low Level Output Voltage 1	V <sub>OL1</sub>	3007	$V_{IL} = 0.3V, V_{IH} = 1.5V$ $I_{OL} = 20\mu A$ $V_{DD} = 2V, V_{SS} = 0V$	-	100	mV
Low Level Output Voltage 2	V <sub>OL2</sub>	3007	$V_{IL} = 0.9V, V_{IH} = 3.15V$ $I_{OL} = 20\mu A$ $V_{DD} = 4.5V, V_{SS} = 0V$	-	100	mV
Low Level Output Voltage 3	V <sub>OL3</sub>	3007	$V_{IL} = 1.2V, V_{IH} = 4.2V$ $I_{OL} = 20\mu A$ $V_{DD} = 6V, V_{SS} = 0V$	-	100	mV
Low Level Output Voltage 4	V <sub>OL4</sub>	3007	$V_{IL} = 0.9V, V_{IH} = 3.15V$ $I_{OL} = 4mA$ $V_{DD} = 4.5V, V_{SS} = 0V$	-	400	mV
Low Level Output Voltage 5	V <sub>OL5</sub>	3007	$V_{IL} = 1.2V, V_{IH} = 4.2V$ $I_{OL} = 5.2mA$ $V_{DD} = 6V, V_{SS} = 0V$	-	400	mV
High Level Output Voltage 1	V <sub>OH1</sub>	3006	$V_{IL} = 0.3V, V_{IH} = 1.5V$ $I_{OH} = -20\mu A$ $V_{DD} = 2V, V_{SS} = 0V$	1.9	-	V
High Level Output Voltage 2	V <sub>OH2</sub>	3006	$V_{IL} = 0.9V, V_{IH} = 3.15V$ $I_{OH} = -20\mu A$ $V_{DD} = 4.5V, V_{SS} = 0V$	4.4	-	V
High Level Output Voltage 3	V <sub>OH3</sub>	3006	$V_{IL} = 1.2V, V_{IH} = 4.2V$ $I_{OH} = -20\mu A$ $V_{DD} = 6V, V_{SS} = 0V$	5.9	-	V
High Level Output Voltage 4	V <sub>OH4</sub>	3006	$V_{IL} = 0.9V, V_{IH} = 3.15V$ $I_{OH} = -4mA$ $V_{DD} = 4.5V, V_{SS} = 0V$	3.7	-	V
High Level Output Voltage 5	V <sub>OH5</sub>	3006	$V_{IL} = 1.2V, V_{IH} = 4.2V$ $I_{OH} = -5.2mA$ $V_{DD} = 6V, V_{SS} = 0V$	5.2	-	V
Input Clamp Voltage 1, to $V_{SS}$	V <sub>IC1</sub>	-	$I_{IN}$ (Under Test) = -100µA $V_{DD}$ = Open, $V_{SS}$ = 0V All Other Pins Open	-0.1	-1.2	V
Input Clamp Voltage 2, to V <sub>DD</sub>	V <sub>IC2</sub>	-	$I_{IN}$ (Under Test) = 100µA $V_{DD}$ = 0V, $V_{SS}$ = Open All Other Pins Open	0.1	1.2	V



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#### 2.3.3 Notes to Electrical Measurement Tables

- 1. Unless otherwise specified all inputs and outputs shall be tested for each characteristic, inputs not under test shall be  $V_{IN} = V_{SS}$  or  $V_{DD}$  and outputs not under test shall be open.
- 2. Functional tests shall be performed with f = 10kHz (min). The maximum time to output comparator strobe =  $30\mu$ s.
- 3. Quiescent Current shall be tested using the following input conditions:
  - (a) All inputs =  $V_{IL}$
  - (b) All inputs =  $V_{IH}$
- 4. Guaranteed but not tested.
- 5. Measurements shall be performed as a go-no-go test on a 100% basis. Read and record measurements shall be performed on a sample of 5 components. The pulse generator shall have the following characteristics: V<sub>GEN</sub> = 0 to V<sub>DD</sub>; f<sub>GEN</sub> = 1MHz minimum; t<sub>r</sub> and t<sub>f</sub> ≤ 6ns (10% to 90%); duty cycle = 50%; Z<sub>out</sub> = 50Ω. Output load capacitance C<sub>L</sub> = 50pF ±5% including scope probe, wiring and stray capacitance without component in the test fixture and output load resistance R<sub>L</sub> = 1kΩ ±5%. Propagation delay shall be measured referenced to the 50% input and output voltages. Transition time shall be measured referenced to the 10% and 90% output voltage.
  6. Read and record measurements shall be performed on a sample of 5 components with 0
- 6. Read and record measurements shall be performed on a sample of 5 components with 0 failures permitted.
- 7. A pulse, having the following conditions shall be applied to the CLK input:  $V_P = 0V$  to  $V_{DD}$ . Maximum clock frequency  $f_{CLK}$  requirement shall be considered as met if proper output state changes occur with the pulse repetition rate set to that given in the Limits column.

#### 2.4 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at  $T_{amb}$  = +22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values ( $\Delta$ ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols		Limits		Units
		Drift	Abso	olute	
		Value Δ	Min	Max	
Quiescent Current	I <sub>DD</sub>	±120	-	400	nA
Low Level Input Current	I <sub>IL</sub>	±20	-	-50	nA
High Level Input Current	I <sub>IH</sub>	±20	-	50	nA
Low Level Output Voltage 4	V <sub>OL4</sub>	±26	-	260	mV
High Level Output Voltage 4	V <sub>OH4</sub>	±0.2	3.98	-	V
Threshold Voltage N-Channel	V <sub>THN</sub>	±0.3	-0.45	-1.45	V
Threshold Voltage P-Channel	V <sub>THP</sub>	±0.3	0.45	1.35	V

#### NOTES:

1. Unless otherwise specified all inputs and outputs shall be tested for each characteristic.



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# 2.5 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at  $T_{amb}$  = +22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values ( $\Delta$ ) shall not be exceeded for each characteristic where specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols		Limits		Units
		Drift	Abso	olute	
		Value Δ	Min	Max	
Functional Test 1	-	-	-	-	-
Functional Test 2	-	-	-	-	-
Functional Test 3	-	-	-	-	-
Quiescent Current	I <sub>DD</sub>	±120	-	400	nA
Low Level Input Current	I <sub>IL</sub>	±20	-	-50	nA
High Level Input Current	I <sub>IH</sub>	±20	-	50	nA
Low Level Output Voltage 4	V <sub>OL4</sub>	±26	-	260	mV
Low Level Output Voltage 5	V <sub>OL5</sub>	±26	-	260	mV
High Level Output Voltage 4	V <sub>OH4</sub>	±0.2	3.98	-	V
High Level Output Voltage 5	V <sub>OH5</sub>	±0.2	5.48	-	V
Threshold Voltage N-Channel	V <sub>THN</sub>	±0.3	-0.45	-1.45	V
Threshold Voltage P-Channel	V <sub>THP</sub>	±0.3	0.45	1.35	V

#### NOTES:

- 1. Unless otherwise specified all inputs and outputs shall be tested for each characteristic.
- 2. The drift values ( $\Delta$ ) are applicable to the Operating Life test only.



#### 2.6 HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS

#### 2.6.1 <u>N-Channel HTRB</u>

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T <sub>amb</sub>	+125 (+0 -5)	°C
Outputs Q, CO	V <sub>OUT</sub>	Open or V <sub>SS</sub>	V
Inputs CLR, CLK, CLKINH	V <sub>IN</sub>	V <sub>SS</sub>	V
Positive Supply Voltage	V <sub>DD</sub>	6 (+0 -0.5)	V
Negative Supply Voltage	V <sub>SS</sub>	0	V
Duration	t	72	Hours

#### NOTES:

- 1. Input Protection Resistor =  $680\Omega$  min to  $47k\Omega$  max.
- 2. Output Load =  $1k\Omega$  min to  $10k\Omega$  max.

# 2.6.2 P-Channel HTRB

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	$T_{amb}$	+125 (+0 -5)	°C
Outputs Q, CO	V <sub>OUT</sub>	Open or V <sub>DD</sub>	V
Inputs CLR, CLK, CLKINH	V <sub>IN</sub>	V <sub>DD</sub>	V
Positive Supply Voltage	$V_{DD}$	6 (+0 -0.5)	V
Negative Supply Voltage	V <sub>SS</sub>	0	V
Duration	t	72	Hours

#### NOTES:

- **1**. Input Protection Resistor =  $680\Omega$  min to  $47k\Omega$  max.
- 2. Output Load =  $1k\Omega$  min to  $10k\Omega$  max.



### 2.7 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T <sub>amb</sub>	+125 (+0 -5)	°C
Outputs Q, CO	V <sub>OUT</sub>	V <sub>DD</sub>	V
Inputs CLR, CLKINH	V <sub>IN</sub>	V <sub>SS</sub>	V
Input CLK	V <sub>IN</sub>	V <sub>GEN</sub>	V
Pulse Voltage	V <sub>GEN</sub>	0V to V <sub>DD</sub>	V
Pulse Frequency Square Wave	f <sub>GEN</sub>	$\begin{array}{l} 100k \pm 10\% \\ 50 \pm 15\% \text{ Duty Cycle} \\ t_r = t_f \leq 400 \text{ns} \end{array}$	Hz
Positive Supply Voltage	V <sub>DD</sub>	6 (+0 -0.5)	V
Negative Supply Voltage	V <sub>SS</sub>	0	V

#### NOTES:

- **1.** Input Protection Resistor =  $680\Omega$  min to  $47k\Omega$  max.
- 2. Output Load =  $1k\Omega$  min to  $10k\Omega$  max.

### 2.8 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.

#### 2.9 TOTAL DOSE RADIATION TESTING

#### 2.9.1 <u>Bias Conditions and Total Dose Level for Total Dose Radiation Testing</u> Continuous bias shall be applied during irradiation testing as specified below.

The total dose level applied shall be as specified in the component type variant information herein or in the Purchase Order.

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T <sub>amb</sub>	+22 ±3	°C
Outputs Q, CO	V <sub>OUT</sub>	Open	V
Inputs CLR, CLK, CLKINH	V <sub>IN</sub>	V <sub>DD</sub>	V
Positive Supply Voltage	V <sub>DD</sub>	6 ±0.3	V
Negative Supply Voltage	V <sub>SS</sub>	0	V

#### NOTES:

1. Input Protection Resistor =  $680\Omega$  min to  $47k\Omega$  max.



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2.9.2 <u>Electrical Measurements for Total Dose Radiation Testing</u> Prior to irradiation testing the devices shall have successfully met Room Temperature Electrical Measurements specified herein.

Unless otherwise stated the measurements shall be performed at  $T_{amb}$  = +22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The parameters to be measured during and on completion of irradiation testing are shown below.

Unless otherwise specified all inputs and outputs shall be tested for each characteristic.

Characteristics	Symbols	Limits		Units	
		Drift	Absolute		
		Value Δ	Min	Max	
Quiescent Current	I <sub>DD</sub>	-	-	40	μA
Threshold Voltage N-Channel	V <sub>THN</sub>	±0.6	-0.4	-1.5	V
Threshold Voltage P-Channel	V <sub>THP</sub>	±0.6	0.4	1.4	V



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## APPENDIX 'A'

#### AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Deviations from Screening Tests - Chart F3	External Visual Inspection: The criteria applicable to chip-outs are those described in MIL-STD-883, Test Method 2009, Paras 3.3.6(b) and 3.3.7(a).
	High Temperature Reverse Bias Burn-in: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.
	Power Burn-in test is performed using STMicroelectronics Specification Ref: 0019255.
	Solderability is not applicable unless specifically stipulated in the Purchase Order.
Deviations from Qualification and Periodic Tests - Chart	External Visual Inspection: The criteria applicable to chip-outs are those described in MIL-STD-883, Test Method 2009, Paras 3.3.6(b) and 3.3.7(a).
F4	Operating Life: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.
Deviations from High and Low Temperatures Electrical Measurements	High and Low Temperatures Electrical Measurements may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes High and Low Temperatures Electrical Measurements per the Detail Specification.
	A summary of the pilot lot testing shall be provided if required by the Purchase Order.
Deviations from Room Temperature Electrical Measurements	All AC characteristics (Capacitance and Timings) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification.
	A summary of the pilot lot testing shall be provided if required by the Purchase Order.